2025년 2월 13일(목), 09:00-10:45
Room H(루비 I), 5층

F. Silicon and Group-IV Devices and Integration Technology 분과

008_[TH1-F] Memory Device Technology

좌장: 이용규 마스터(삼성전자), 김경록 교수(울산과학기술원)

초청 TH1-F-1 09:00-09:30	Evolution of Flash Memory Device Technology in AI Era Suk-Kang Sung Samsung Electronics Co., Ltd.
TH1-F-2 09:30-09:45	Self-Defect Compensated IGZO/ITO Capacitors for Memory Applications Sumin Han and Changhwan Shin School of Electrical Engineering, Korea University
TH1-F-3 09:45-10:00	V_t Tuning Without Memory Window Reduction in HZO-based FeFET Using Fluorine Surface Treatment for High-Performance Analog In-Memory Computing Kyungsoo Park, Chulwon Chung, Seung Hyun Yoon, Junhyeok Park, and Changhwan Choi Division of Materials Science and Engineering, Hanyang University
TH1-F-4 10:00-10:15	A Study on the Neuromorphic Synaptic Characteristics of Mesh-Type Floating Gate Transistors So Yeon Jeong[1], Jae Min Kim[1], Hyeong Jin Chae[1], Tae Hwan Koo[1], Ju Yeong Chae[1], Hyeon Seok Jeong[1], and Moon Gyu Jang[1,2] [1]School of Nano Convergence Technology, Hallym University, [2]Nano Convergence Technology Center, Hallym University
TH1-F-5 10:15-10:30	Design of Current Sense Amplifier for SRAM Consisting of a Feedback Field-Effect Transistor Jong Hyeok Oh and Yun Seop Yu Major of ICT & Robotics Eng., Hankyong National University

H1-F-6 10:30-10:45	Top-Gate Oxide Semiconductor FETs for Reliable 2T0C Read/Write Operation with Reduced Capacitive Coupling Minho Park[1], Hyeonho Gu[1], Hyeonjin Lee[2], Yongwoo Lee[1], and Jimin Kwon[1,2] [1]Department of Electrical Engineering, UNIST, [2]Graduate School of Semiconductor Materials and Devices Engineering, UNIST